

## 600V, 20A, Trench FS II Fast IGBT

### General Description:

Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

### Features

Trench FSII Technology offering

- Very low  $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in  $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

### Application

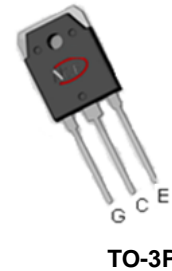
- Air Condition
- Inverters
- Motor drives



Schematic diagram

### Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE20TH60BP	TO-3P	NCE20TH60BP



TO-3P

### Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate- Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current	40	A
	Collector Current @ $T_c = 100^\circ\text{C}$	20	A
$I_{Cplus}$	Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	60	A
-	turn off safe operating area, $V_{CE}=600\text{V}$ , $T_j=150^\circ\text{C}$	60	A
$I_F$	Diode Continuous Forward Current @ $T_c = 100^\circ\text{C}$	10	A
$I_{FM}$	Diode Maximum Forward Current	30	A
$P_D$	Power Dissipation @ $T_c = 25^\circ\text{C}$	135	W
	Power Dissipation @ $T_c = 100^\circ\text{C}$	54	W
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^\circ\text{C}$
$t_{sc}$	Short circuit withstand time $V_{GE}=15.0\text{V}$ , $V_{CC} \leq 400\text{V}$ , Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ , $T_j \leq 150^\circ\text{C}$	3	us

**Thermal Characteristic**

Symbol	Parameter	Value	Units
R <sub>θJC</sub>	Thermal Resistance, Junction to case for IGBT	0.93	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction to case for Diode	1.92	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	62	°C/W

**Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
<b>STATIC Characteristics</b>						
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	V <sub>GE</sub> =0V, I <sub>CE</sub> =1mA	600	--	--	V
I <sub>CES</sub>	Collector-Emitter Leakage Current	V <sub>GE</sub> =0V, V <sub>CE</sub> =600V	--	--	4	uA
I <sub>GES(F)</sub>	Gate to Emitter Forward Leakage	V <sub>GE</sub> =+30V, V <sub>CE</sub> =0V	--	--	100	nA
I <sub>GES(R)</sub>	Gate to Source Reverse Leakage	V <sub>GE</sub> =-30V, V <sub>CE</sub> =0V	--	--	100	nA
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =20A, T <sub>J</sub> =25°C	--	1.7	1.9	V
		V <sub>GE</sub> =15V, T <sub>J</sub> =100°C	--	1.9	--	V
V <sub>GE(th)</sub>	Gate Threshold Voltage	I <sub>C</sub> =1mA, V <sub>CE</sub> =V <sub>GE</sub>	4.0	--	6.0	V
<b>Dynamic Characteristics</b>						
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz	--	2580	--	pF
C <sub>oes</sub>	Output Capacitance		--	48	--	
C <sub>res</sub>	Reverse Transfer Capacitance		--	26	--	
Q <sub>g</sub>	Total Gate Charge	V <sub>CC</sub> =480V, I <sub>C</sub> =20A V <sub>GE</sub> =15V	--	97	--	nC
Q <sub>ge</sub>	Gate to Emitter Charge		--	17	--	nC
Q <sub>gc</sub>	Gate to Collector Charge		--	37	--	nC
I <sub>C(SC)</sub>	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V <sub>GE</sub> =15V, V <sub>CC</sub> ≤400V, t <sub>sc</sub> ≤3us, T <sub>J</sub> ≤150°C	--	130	--	A
<b>Switching Characteristics</b>						
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>CE</sub> =400V, I <sub>C</sub> =10A V <sub>GE</sub> =0/15V, R <sub>g</sub> =25Ω Inductive Load	--	18	--	ns
t <sub>r</sub>	Rise Time		--	16	--	
t <sub>d(OFF)</sub>	Turn-Off Delay Time		--	164	--	
t <sub>f</sub>	Fall Time		--	15	--	
E <sub>on</sub>	Turn-On Switching Loss		--	0.43	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	0.17	--	
E <sub>ts</sub>	Total Switching Loss		--	0.60	--	

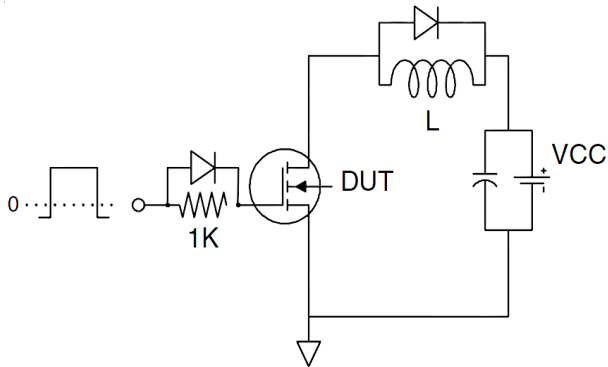
**Electrical Characteristics of the Diode (T<sub>C</sub>= 25°C unless otherwise specified):**

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> =10A	--	1.45	1.7	V
T <sub>rr</sub>	Reverse Recovery Time	V <sub>CC</sub> =400V, I <sub>F</sub> =10A, di/dt=200A/uS	--	182	--	ns
I <sub>RRM</sub>	Diode Peak Reverse Recovery Current		--	5.3	--	A
Q <sub>rr</sub>	Reverse Recovery Charge		--	0.5	--	uC

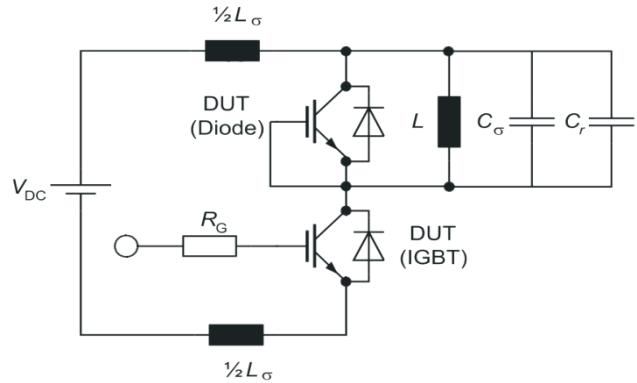
Pulse width t<sub>tp</sub>≤380μs, δ≤2%

### Test Circuit

#### 1) Gate Charge Test Circuit

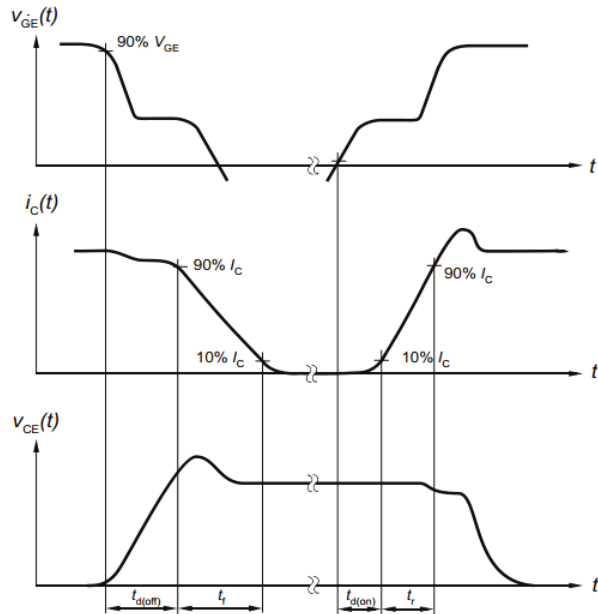


#### 2) Switch Time Test Circuit

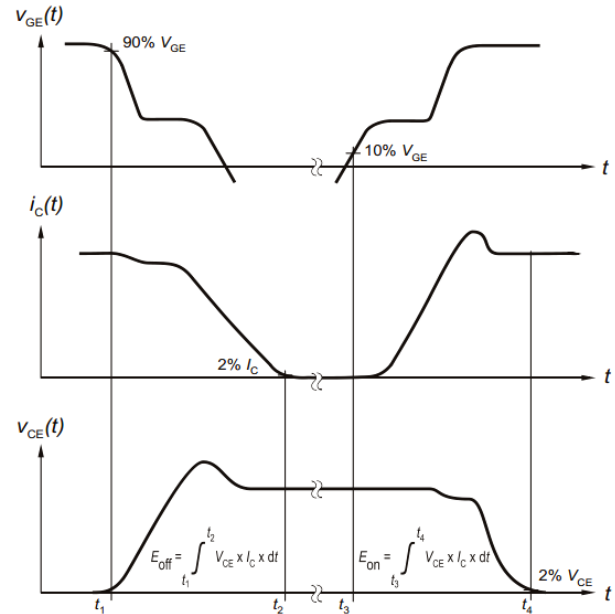


### Switching characteristics

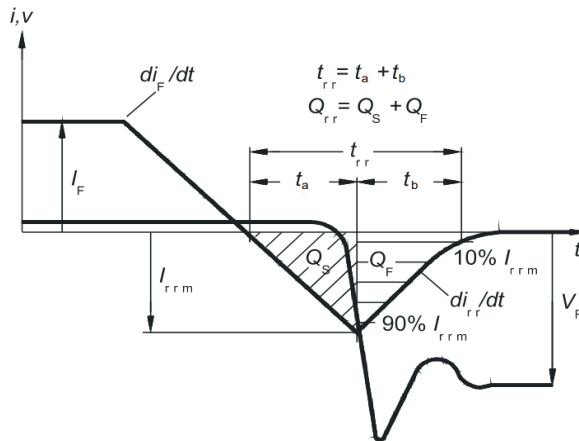
#### 1) definition of switching times



#### 2) definition of switching losses



#### 3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

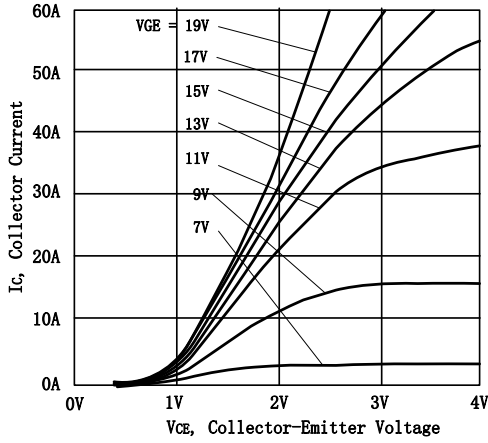


Figure 2 Transfer Characteristics

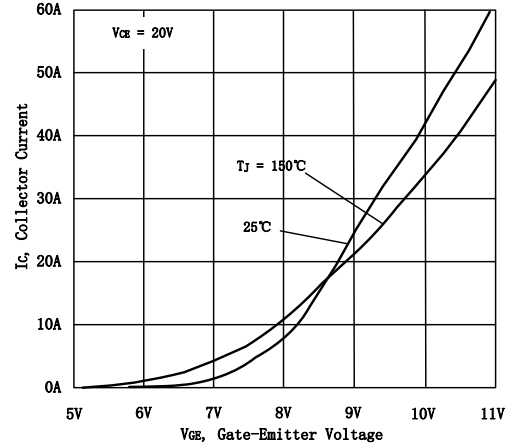


Figure 3  $V_{CEsat}$  vs. Case Temperature

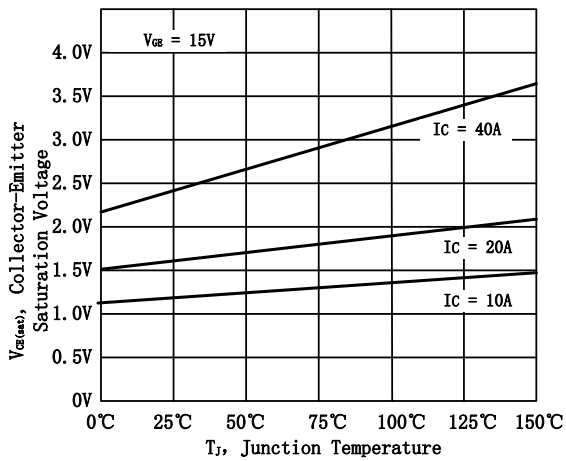


Figure 4 Saturation Voltage vs. VGE

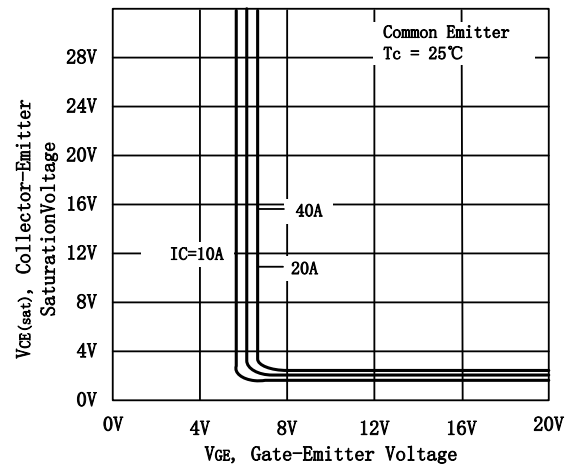


Figure 5 Capacitance Characteristics

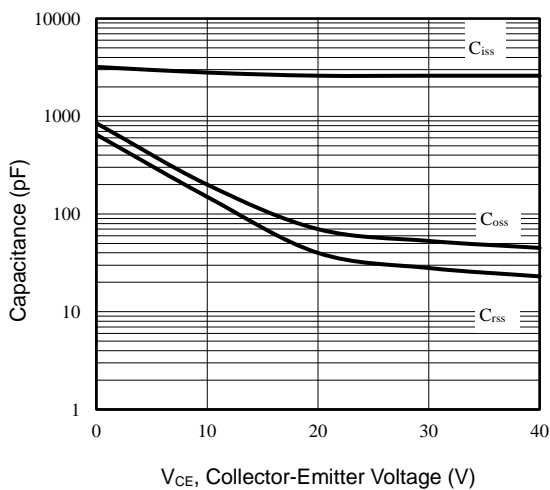
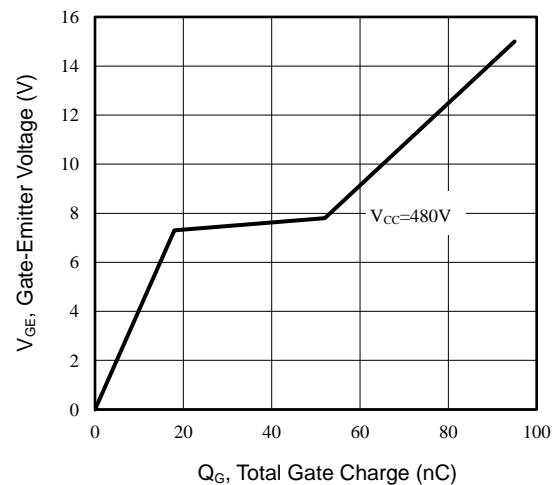


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics (continued)

Figure 7 Forward Characteristics

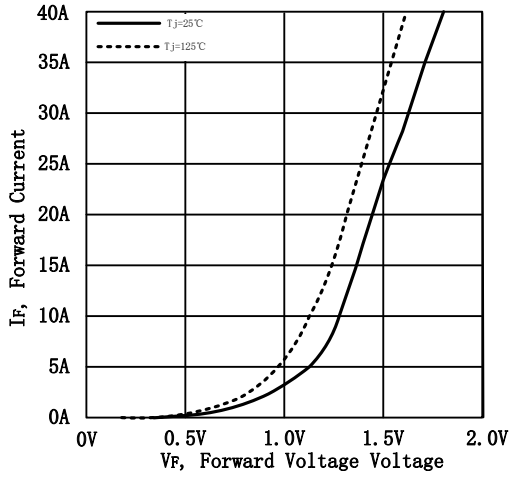


Figure 8 VF vs. temperature

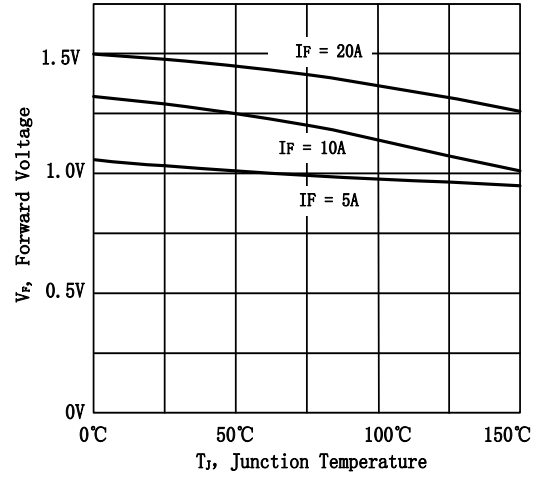


Figure 9 Forward Bias Safe Operating

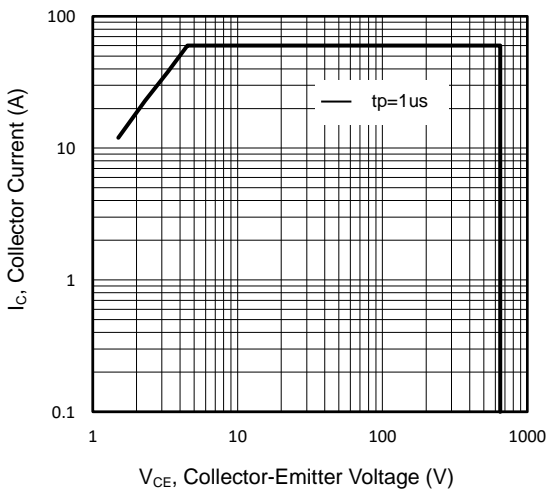


Figure 10 Gate-emitter Threshold Voltage as a Function of Junction Temperature

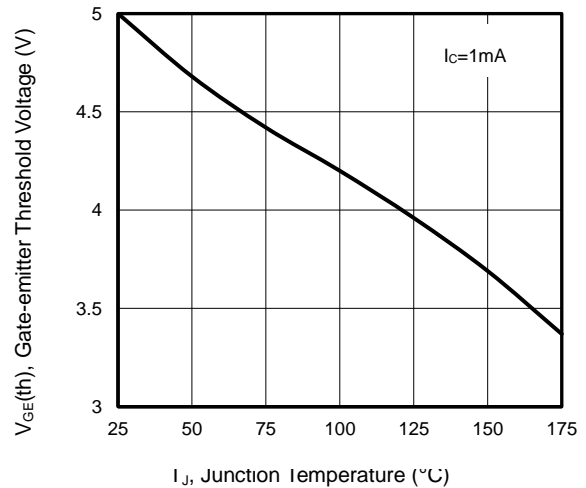


Figure 11 Typical Switching Times as a Function of Gate Resistor

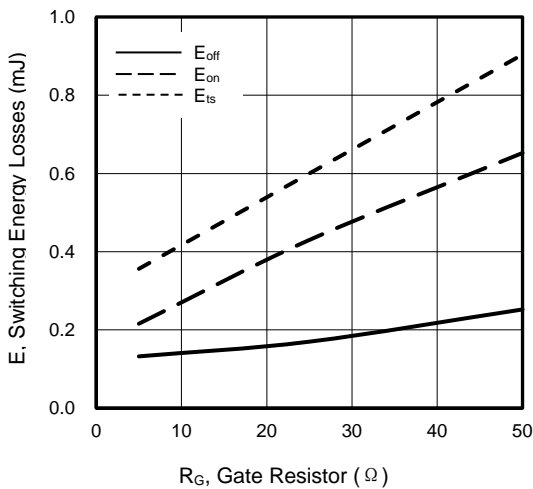
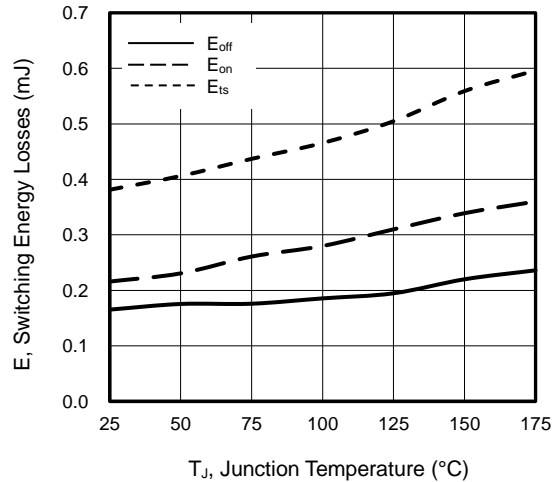


Figure 12 Typical Switching Times as a Function of Junction Temperature



Typical Electrical and Thermal Characteristics (continued)

Figure 13 Power Dissipation as a Function of Case Temperature

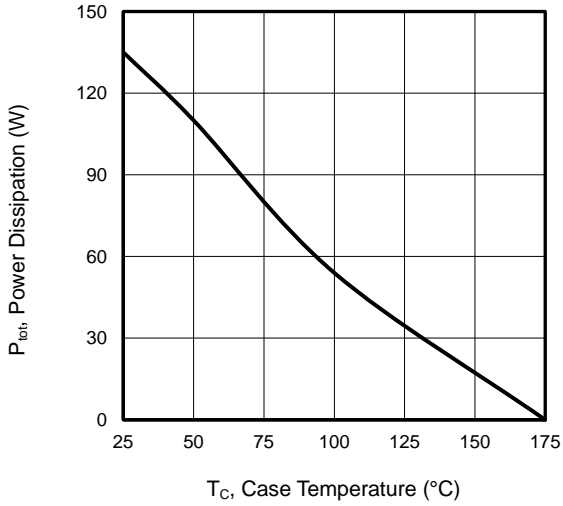


Figure 14 Current Derating

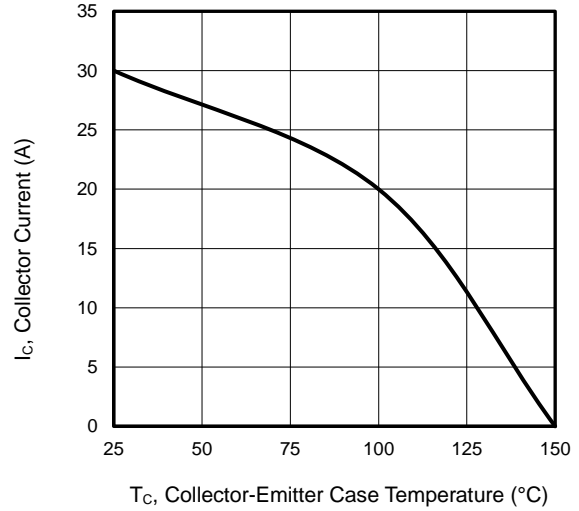


Figure 15 Typical Collector-emitter Saturation Voltage as a function of Collector Current

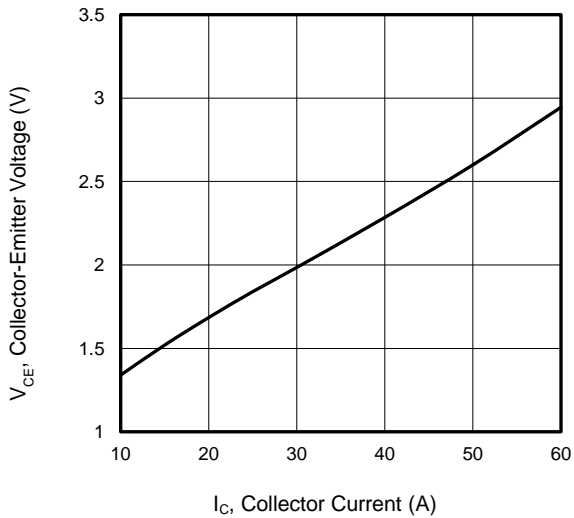
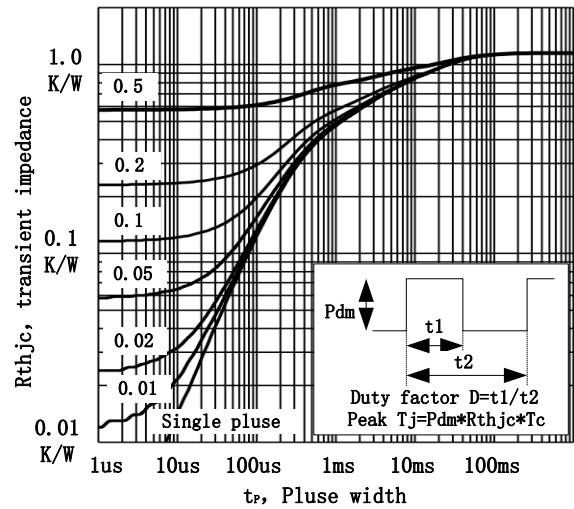
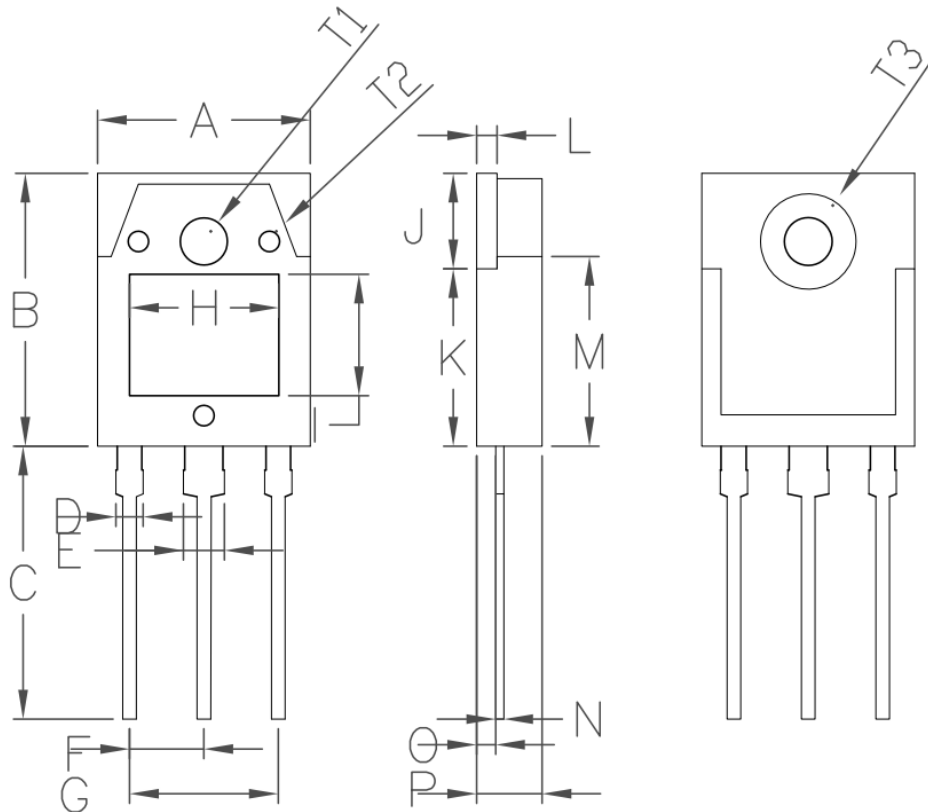


Figure 16 Transient Thermal Impedance



## TO-3P-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	15.50	15.70	0.61	0.62
B	19.70	20.10	0.78	0.79
C	20.10	20.50	0.79	0.81
D	2.00		0.08	
E	3.00		0.12	
F	5.45		0.21	
G	10.90		0.43	
H	10.80	11.00	0.43	0.43
I	8.80	9.00	0.35	0.35
J	6.85	7.15	0.27	0.28
K	12.75	13.05	0.50	0.51
L	1.49	1.51	0.06	0.06
M	13.70	14.00	0.54	0.55
N	0.59	0.61	0.02	0.02
O	1.32	1.48	0.05	0.06
P	4.70	4.90	0.19	0.19
S	4°		0.16°	
T1	3.50		0.14	
T2	1.50		0.06	
T3	7.00		0.28	

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